Abstracts

W-band InP wideband MMIC LNA with 30 K noise temperature

S. Weinreb, R. Lai, N. Erickson, T. Gaier and J. Wielgus. "W-band InP wideband MMIC LNA with 30 K noise temperature." 1999 MTT-S International Microwave Symposium Digest 99.1 (1999 Vol. I [MWSYM]): 101-104 vol.1.

This paper describe a millimeter wave low noise amplifier with extraordinary low noise, low power consumption, and wide frequency range. These results are achieved utilizing state-of-the-art InP HEMTs coupled with CPW circuit design. The paper describes the transistor model, as well as modeled and measured on-wafer and in-module results at both 300 K and 24 K operating temperatures for several samples of the device.

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